

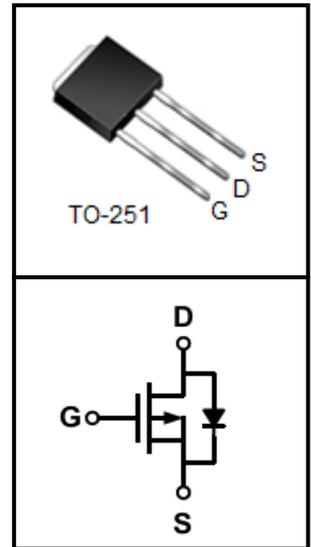
100V P-Channel Trench MOSFET

FEATURES

- Super Low Gate Charge
- 100% EAS Guaranteed
- RoHS compliant
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Hard switched and high frequency circuits



Device Marking and Package Information

Device	Package	Marking
CTU10P060	TO-251	CTU10P060

Absolute Maximum Ratings at $T_j = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	-100	V
Continuous Drain Current $T_C = 25^\circ\text{C}$ (note1)	I_D	-40	A
Continuous Drain Current $T_C = 100^\circ\text{C}$ (note1)		-28	A
Pulsed Drain Current (note2)	I_{DM}	-72	A
Gate Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note3)	E_{AS}	240	mJ
Power Dissipation $T_C = 25^\circ\text{C}$ (note4)	P_D	74.9	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+175	$^\circ\text{C}$

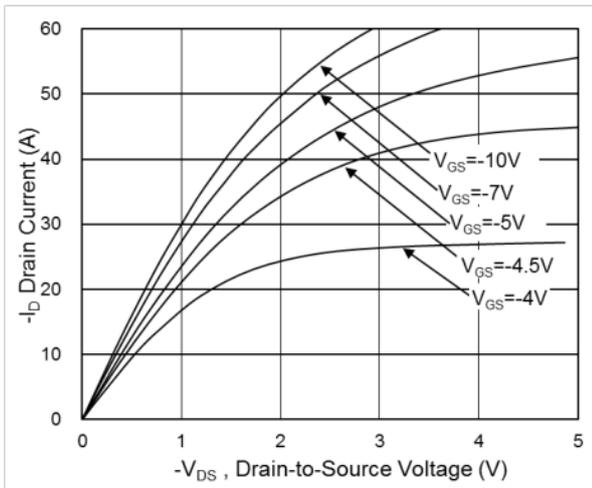
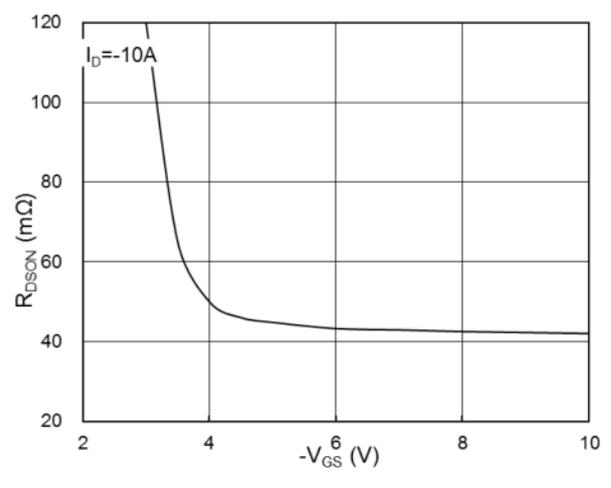
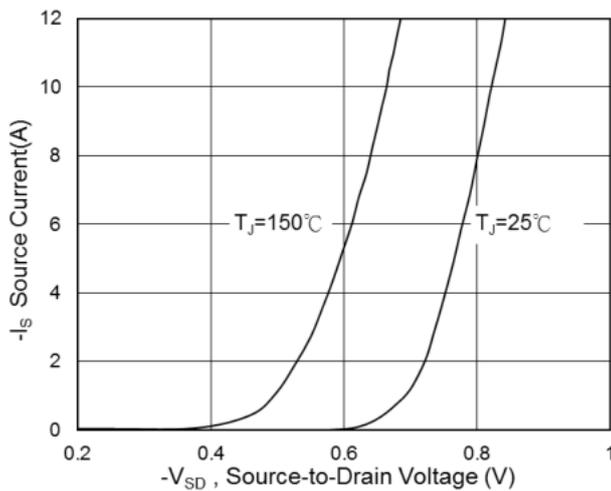
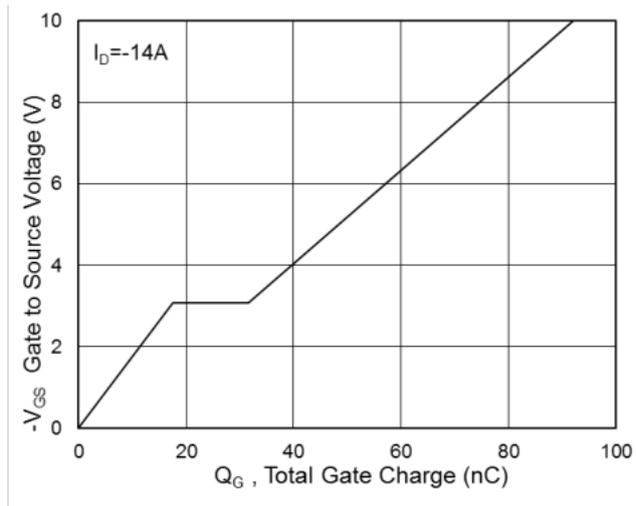
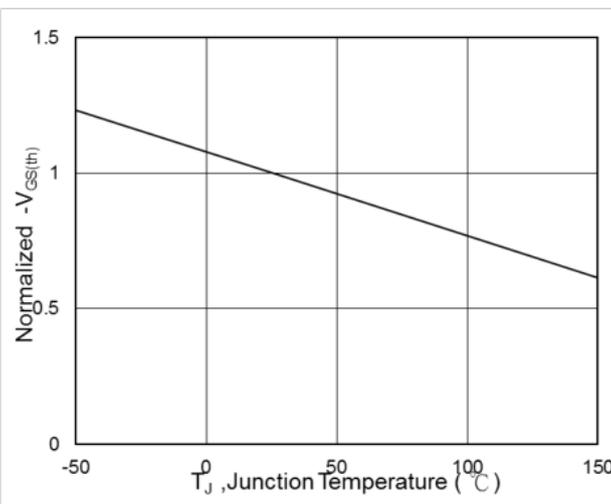
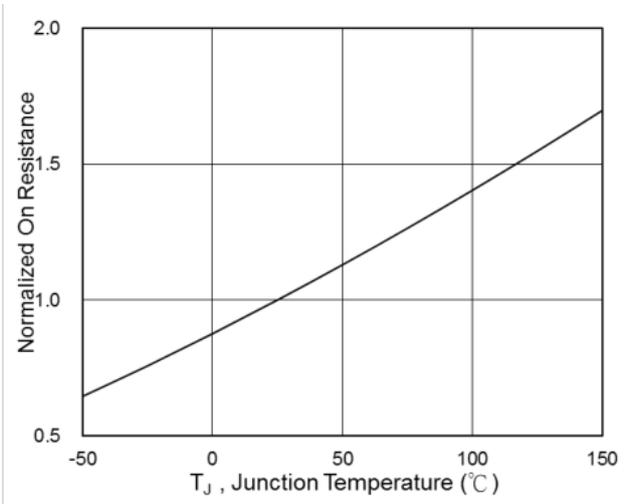
Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-Case (note1)	$R_{\theta JC}$	1.2	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (note1)	$R_{\theta JA}$	62	$^\circ\text{C/W}$

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise specified						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	-100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	-50	μA
		$V_{DS} = -100V, V_{GS} = 0V, T_J = 55^\circ\text{C}$	--	--	-60	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.2	--	-2.5	V
Drain-Source On-Resistance (note2)	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -12A$	--	46	60	$m\Omega$
		$V_{GS} = -4.5V, I_D = -9A$	--	48	68	$m\Omega$
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -25V, f = 1.0MHz$	--	6516	--	pF
Output Capacitance	C_{oss}		--	223	--	
Reverse Transfer Capacitance	C_{rss}		--	125	--	
Total Gate Charge (4.5V)	Q_g	$V_{DD} = -80V, I_D = -15A, V_{GS} = -10V$	--	92	--	nC
Gate-Source Charge	Q_{gs}		--	17.5	--	
Gate-Drain Charge	Q_{gd}		--	14	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = -50V, I_D = -15A, V_{GS} = -10V, R_G = 3.3\Omega$	--	20.5	--	ns
Turn-on Rise Time	t_r		--	32.2	--	
Turn-off Delay Time	$t_{d(off)}$		--	123	--	
Turn-off Fall Time	t_f		--	63.7	--	
Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	-40	A
Pulsed Diode Forward Current	I_{SM}		--	--	-72	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = -1A, V_{GS} = 0V$	--	--	1.2	V
Reverse Recovery Time	t_{rr}	$I_F = -14A, di_F/dt = 100A/\mu s$	--	31.2	--	ns
Reverse Recovery Charge	Q_{rr}		--	31.97	--	nC

Notes

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The EAS data shows Max. rating . The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.85mH$
4. The power dissipation is limited by 175 $^\circ\text{C}$ junction temperature
5. The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Fig.1 Typical Output Characteristics

Fig.2 On-Resistance vs. G-S Voltage

Fig.3 Forward Characteristics of Reverse Diode

Fig.4 Gate-Charge Characteristics

Fig.5 Normalized $V_{GS(th)}$ vs. T_J

Fig.6 Normalized $R_{DS(on)}$ vs. T_J

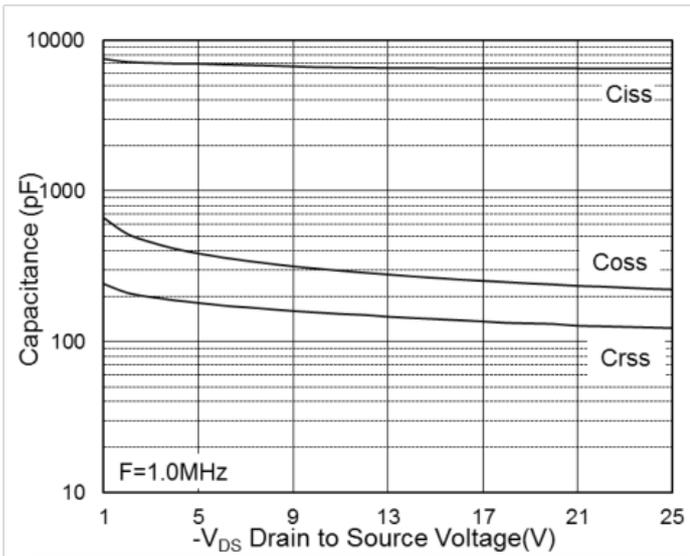
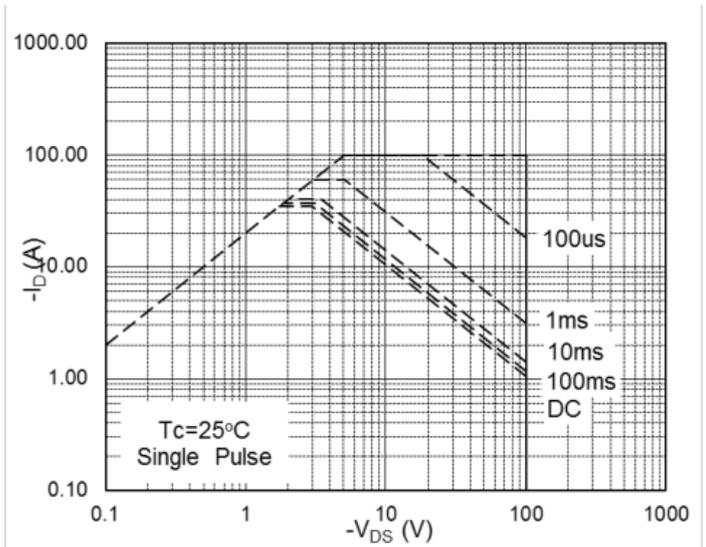
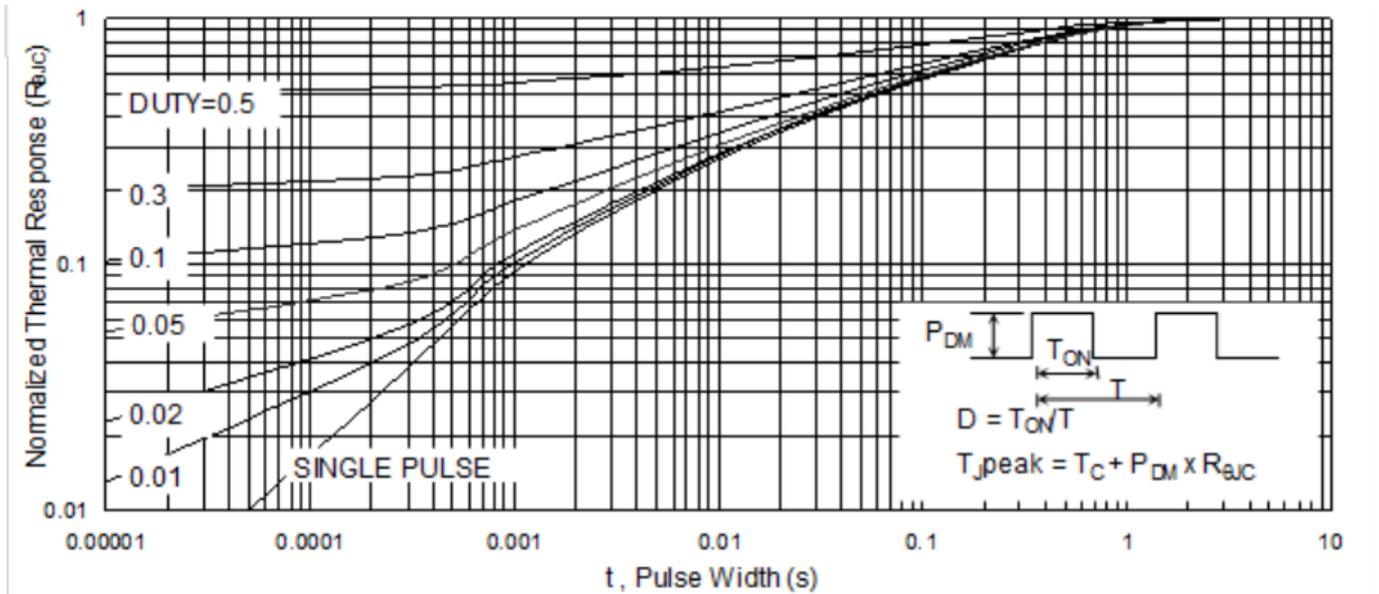
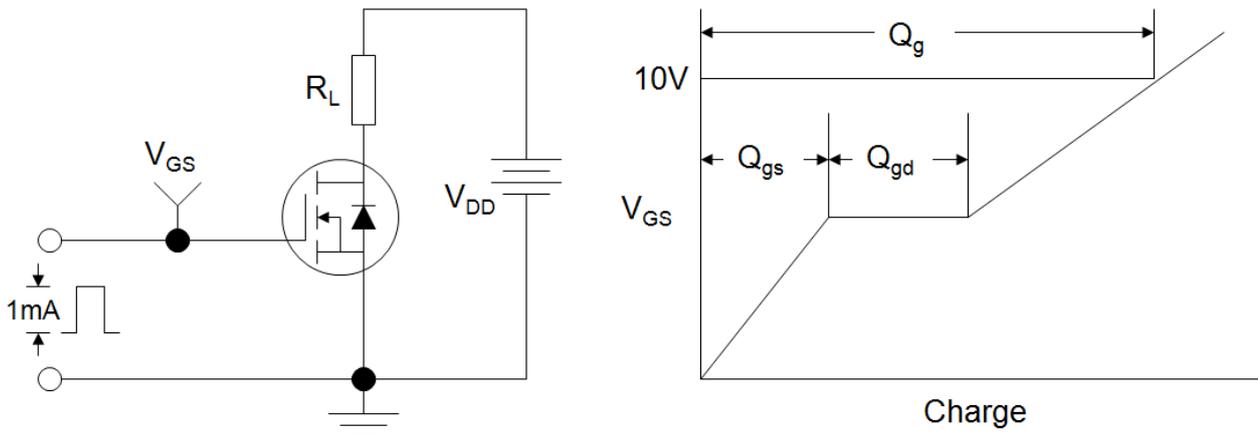
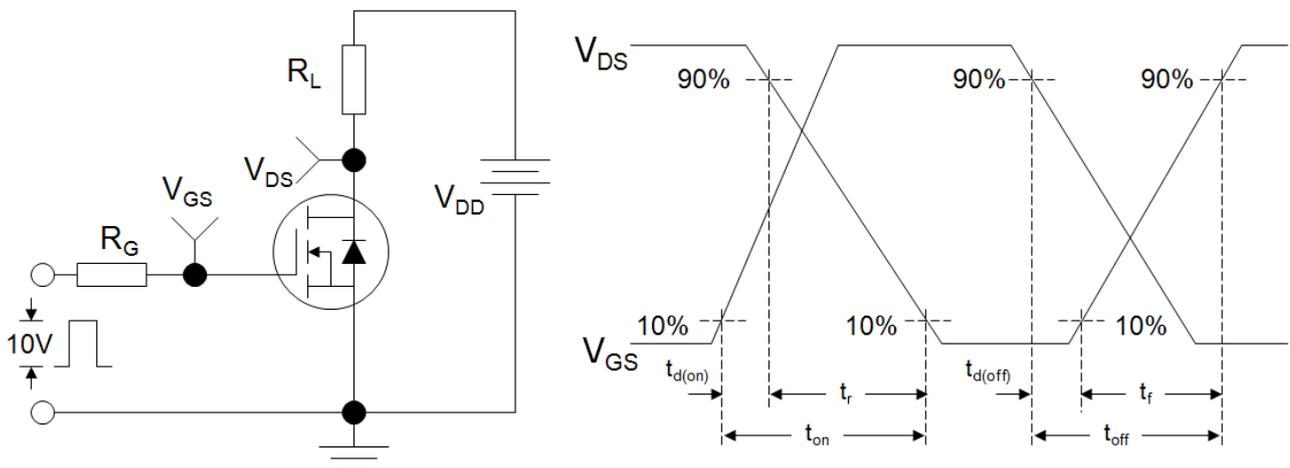
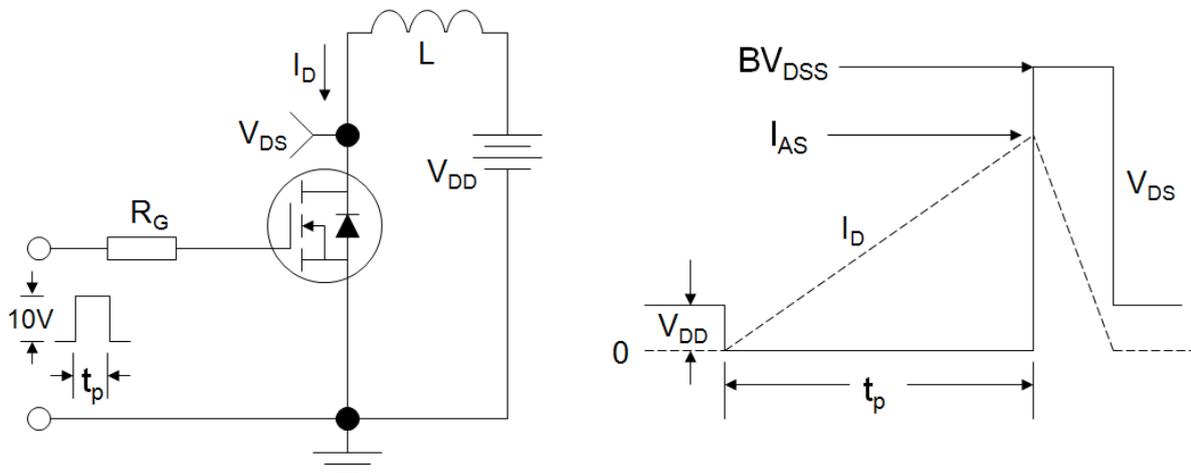
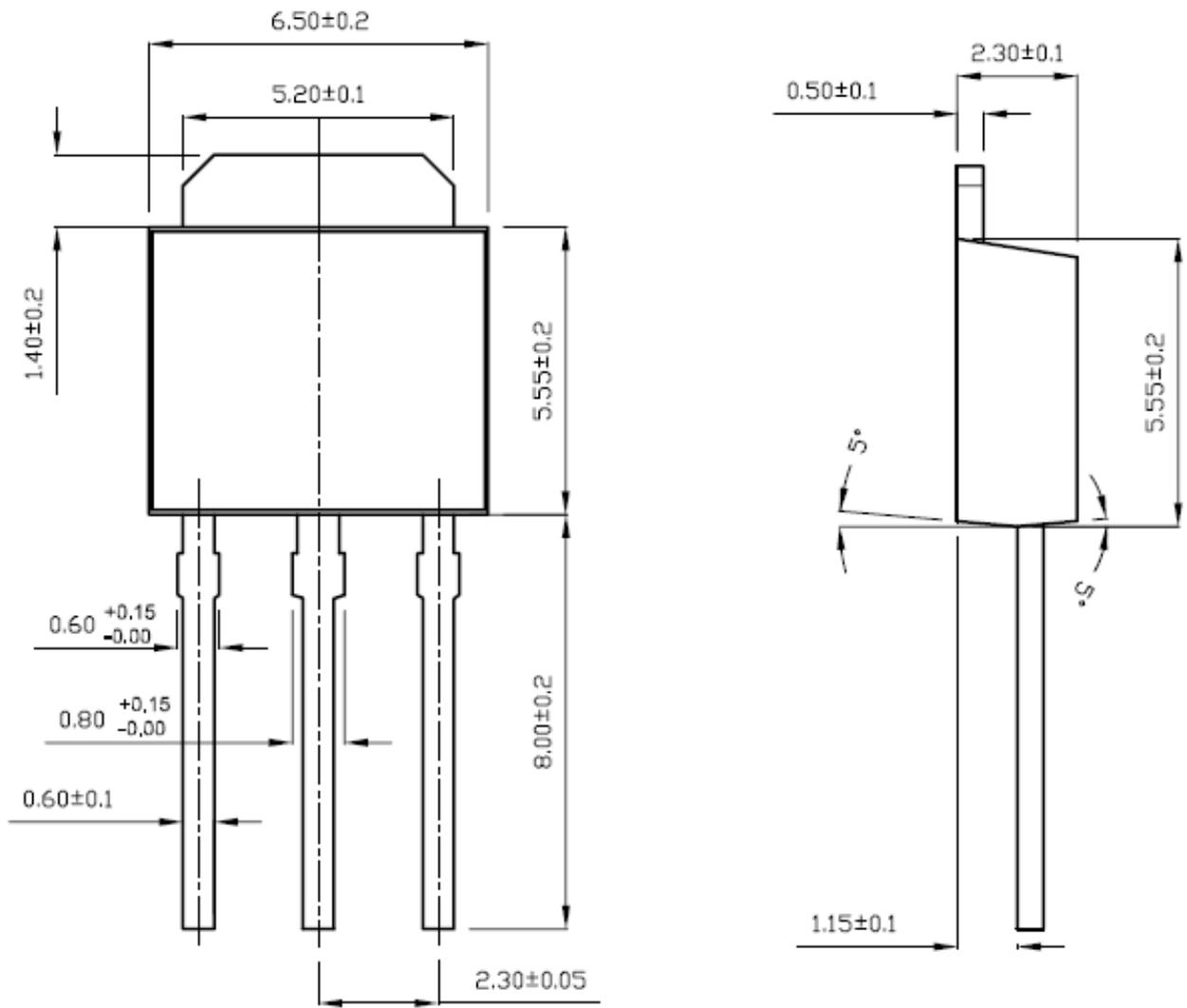
Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

Figure A: Gate Charge Test Circuit and Waveform

Figure B: Resistive Switching Test Circuit and Waveform

Figure C: Unclamped Inductive Switching Test Circuit and Waveform


TO-251



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